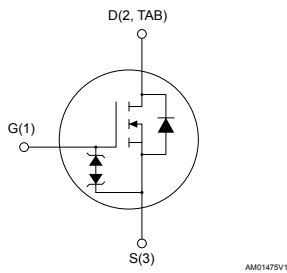
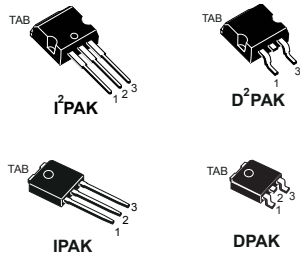




**THE DATASHEET OF  
STB4NK60ZT4**



## N-channel 600 V, 1.7 $\Omega$ typ., 4 A SuperMESH™ Power MOSFETs in I<sup>2</sup>PAK, D<sup>2</sup>PAK, IPAK and DPAK packages



### Features

Order codes	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	P <sub>TOT</sub>	I <sub>D</sub>
STB4NK60Z-1	600 V	2 $\Omega$	70 W	4 A
STB4NK60ZT4				
STD4NK60Z-1				
STD4NK60ZT4				

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Zener-protected

### Applications

- Switching applications

### Description

These high-voltage devices are Zener-protected N-channel Power MOSFETs developed using the SuperMESH™ technology by STMicroelectronics, an optimization of the well-established PowerMESH™. In addition to a significant reduction in on-resistance, these devices are designed to ensure a high level of dv/dt capability for the most demanding applications.

Product status
STB4NK60Z-1
STB4NK60ZT4
STD4NK60Z-1
STD4NK60ZT4

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	600	V
$V_{GS}$	Gate-source voltage	±30	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ °C}$	4	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ °C}$	2.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	16	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	70	W
ESD	Gate-source human body model (C=100 pF, R=1.5 kΩ)	3	kV
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
$T_j$	Operating junction temperature range	-55 to 150	°C
$T_{stg}$	Storage temperature range		

1. Pulse width limited by safe operating area.

2.  $I_{SD} \leq 4\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ .

**Table 2. Thermal data**

Symbol	Parameter	Value		Unit
		I <sup>2</sup> PAK, D <sup>2</sup> PAK	IPAK, DPAK	
$R_{thj-case}$	Thermal resistance junction- case	1.79		°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	100	°C/W

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	4	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	120	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	600			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}, T_C = 125\text{ °C}^{(1)}$			50	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}, I_D = 2\text{ A}$		1.7	2	$\Omega$

1. Defined by design, not subject to production test.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0\text{ V}$	-	510		pF
$C_{oss}$	Output capacitance			67		
$C_{riss}$	Reverse transfer capacitance			13		
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 0\text{ V to } 480\text{ V}$	-	38.5		
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}, I_D = 2\text{ A}, R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 13. Test circuit for resistive load switching times)	-	12		ns
$t_r$	Rise time			9.5		
$t_{d(off)}$	Turn-off delay time			29		
$t_f$	Fall time			16.5		
$t_{r(Voff)}$	Off-voltage rise time			12		
$t_r$	Fall time	$V_{DD} = 480\text{ V}, I_D = 4\text{ A}, R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	12		
$t_c$	Cross-over time			19.5		
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}, I_D = 4\text{ A}, V_{GS} = 0\text{ to } 10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	18.8	26	nC
$Q_{gs}$	Gate-source charge			3.8		
$Q_{gd}$	Gate-drain charge			9.8		

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

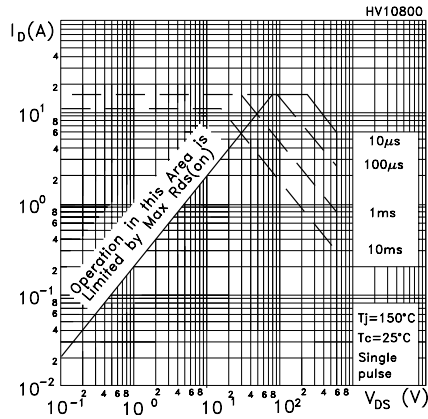
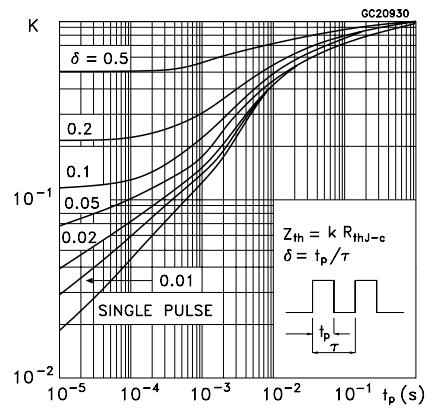
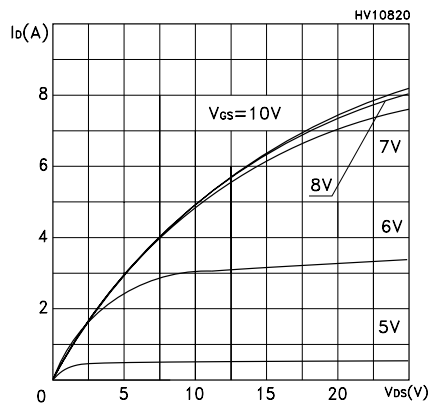
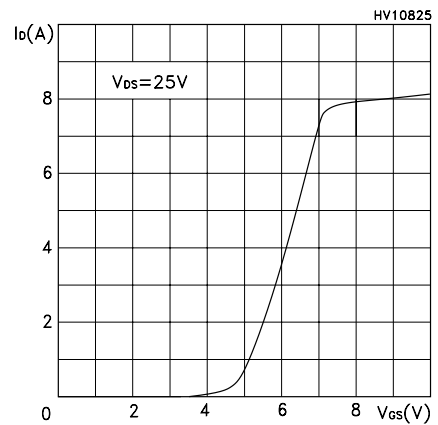
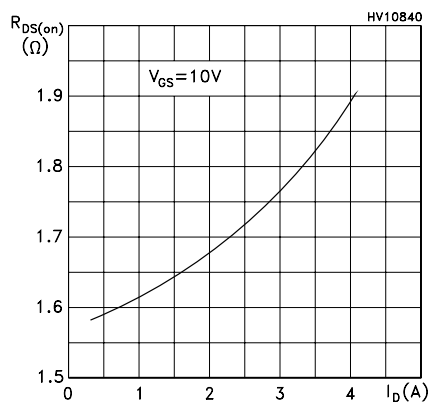
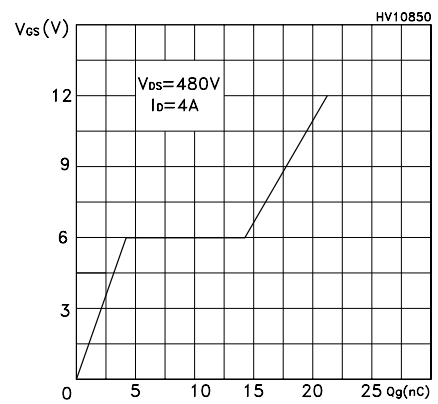
**Table 6. Source-drain diode**

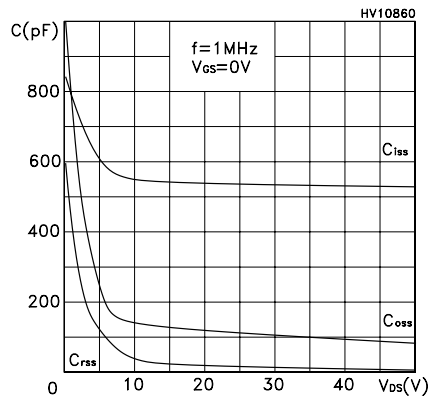
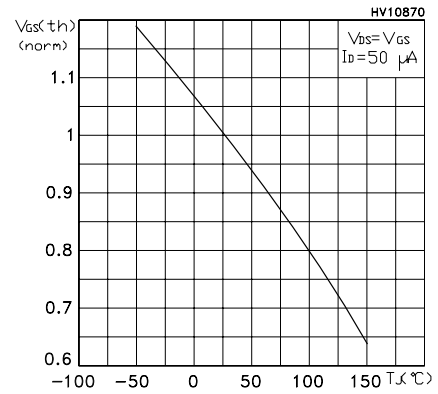
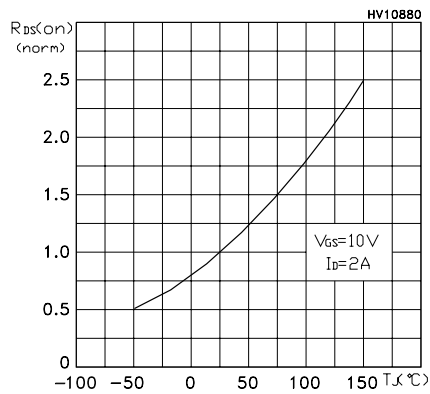
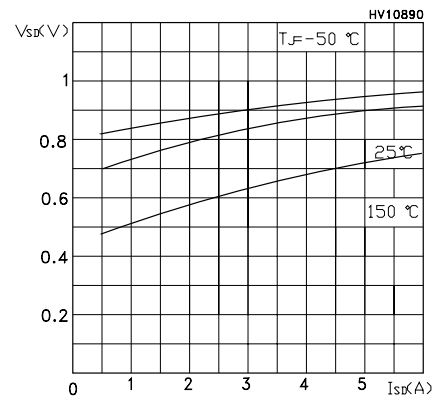
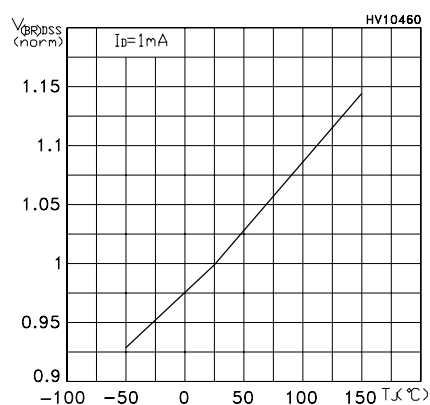
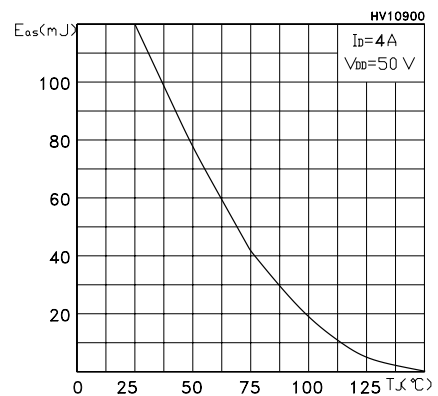
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		4	A
$I_{SDM}$	Source-drain current (pulsed)		-		16	
$V_{SD}$	Forward on voltage	$I_{SD} = 4\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 4\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	400		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 24\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$	-	1.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	8.5		A

**Table 7. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0\text{ A}$	$\pm 30$	-	-	V

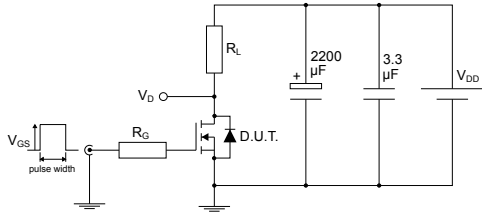
The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

**2.1 Electrical characteristics (curves)**
**Figure 1. Safe operating area**

**Figure 2. Thermal impedance**

**Figure 3. Output characteristics**

**Figure 4. Transfer characteristics**

**Figure 5. Static drain-source on-resistance**

**Figure 6. Gate charge vs gate-source voltage**


**Figure 7. Capacitance variations**

**Figure 8. Normalized gate threshold voltage vs temperature**

**Figure 9. Normalized on-resistance vs temperature**

**Figure 10. Source-drain diode forward characteristic**

**Figure 11. Normalized  $V_{(BR)DSS}$  vs temperature**

**Figure 12. Maximum avalanche energy vs temperature**


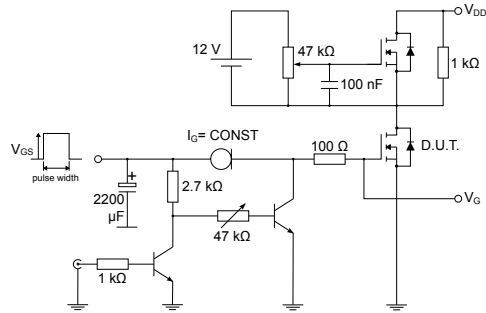
### 3 Test circuits

Figure 13. Test circuit for resistive load switching times



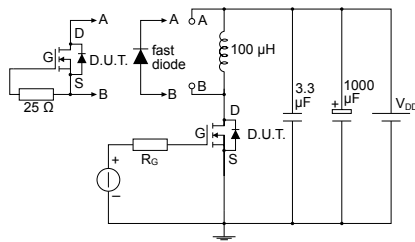
AM01468v1

Figure 14. Test circuit for gate charge behavior



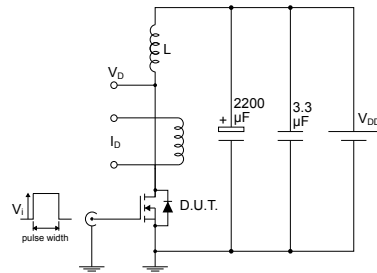
AM01469v1

Figure 15. Test circuit for inductive load switching and diode recovery times



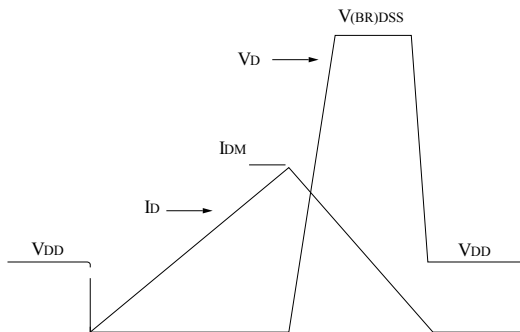
AM01470v1

Figure 16. Unclamped inductive load test circuit



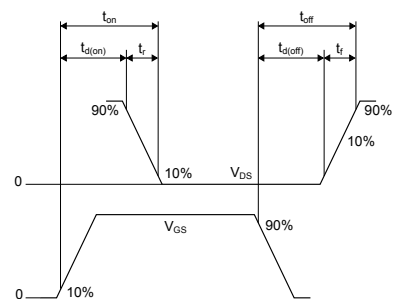
AM01471v1

Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



AM01473v1



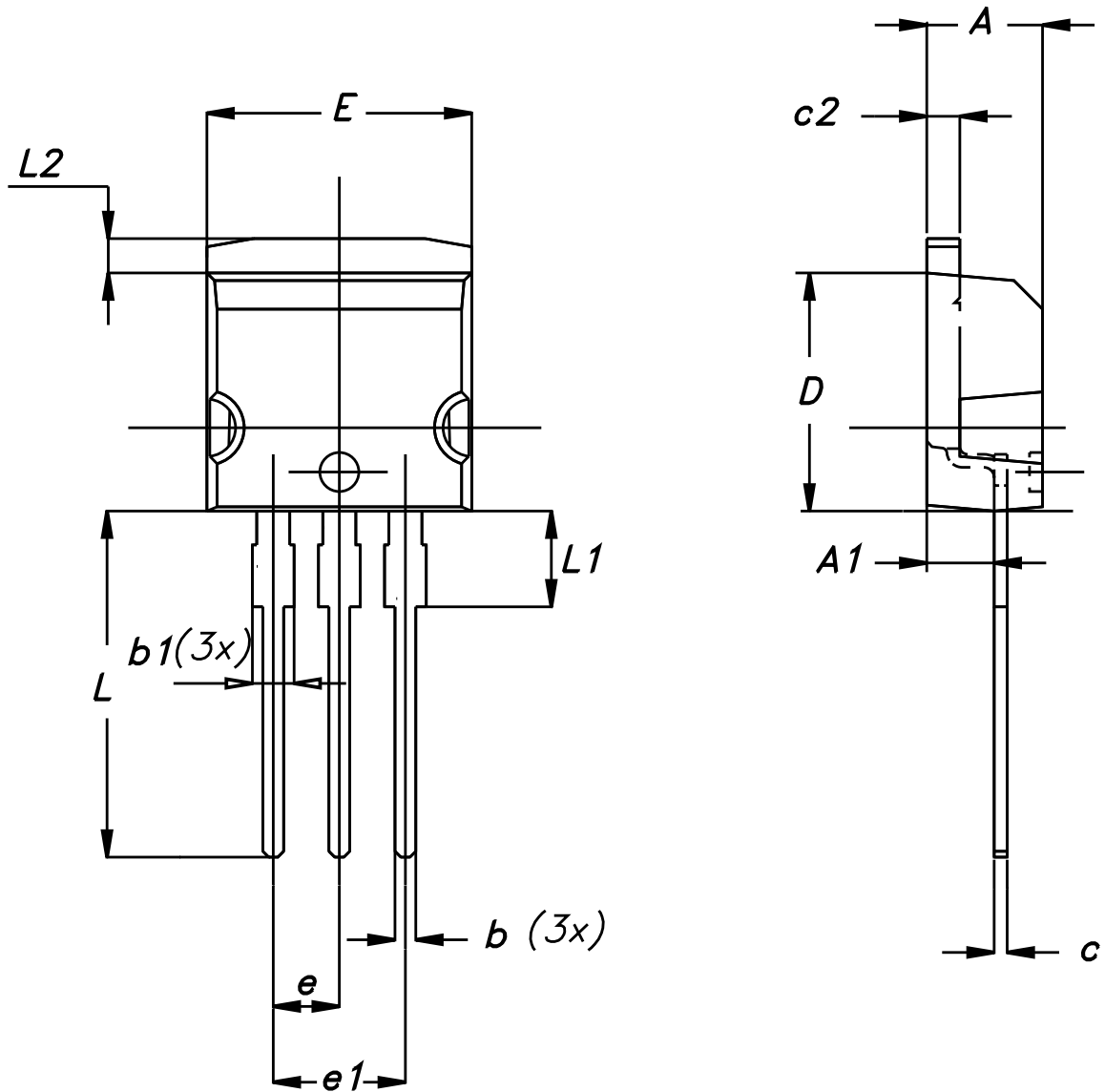
## 4 Package information

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In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

4.1 I<sup>2</sup>PAK package information

Figure 19. I<sup>2</sup>PAK package outline



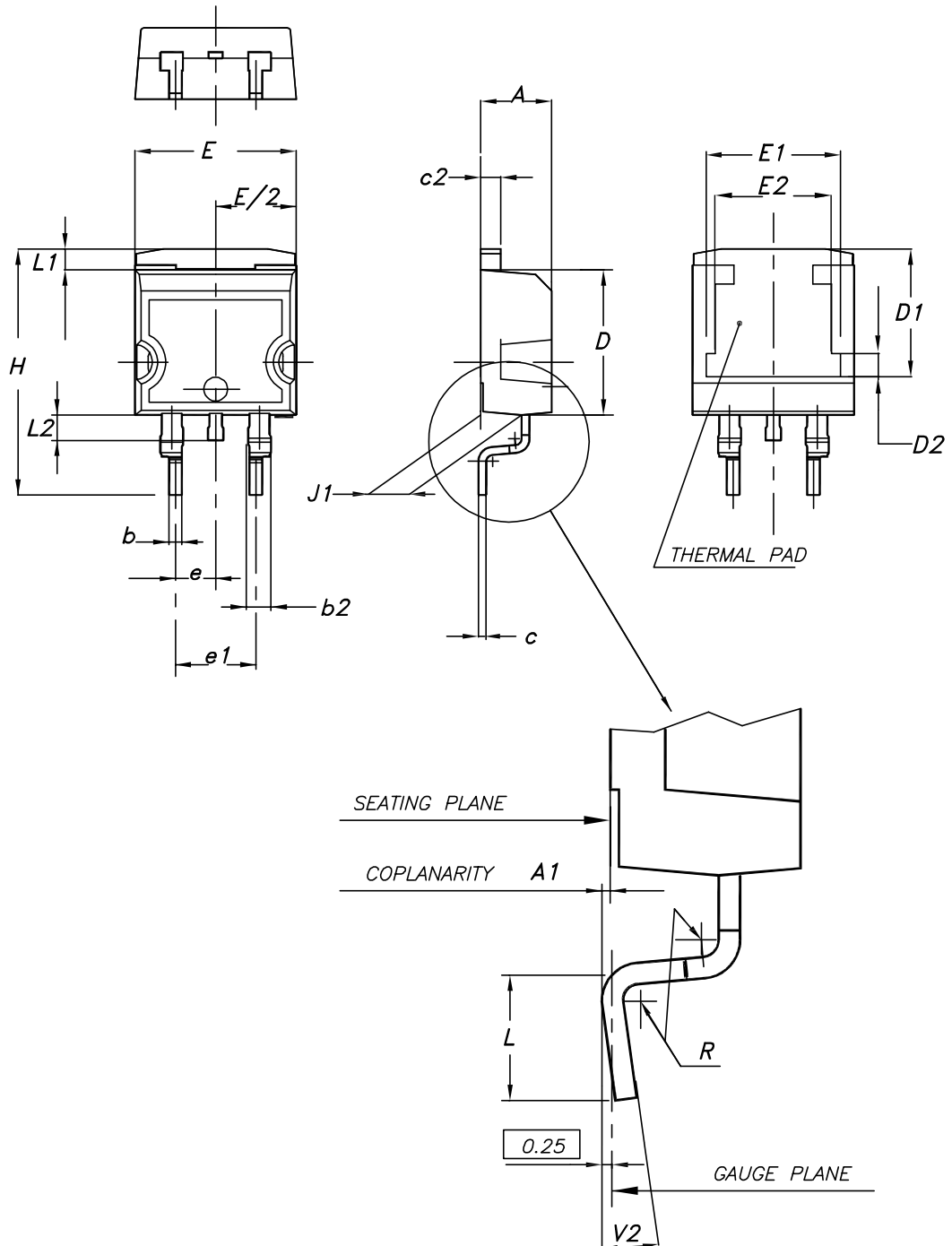
0004982\_Rev\_H

**Table 8. I<sup>2</sup>PAK package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40	-	4.60
A1	2.40	-	2.72
b	0.61	-	0.88
b1	1.14	-	1.70
c	0.49	-	0.70
c2	1.23	-	1.32
D	8.95	-	9.35
e	2.40	-	2.70
e1	4.95	-	5.15
E	10	-	10.40
L	13	-	14
L1	3.50	-	3.93
L2	1.27	-	1.40

## 4.2 D<sup>2</sup>PAK (TO-263) type A package information

Figure 20. D<sup>2</sup>PAK (TO-263) type A package outline



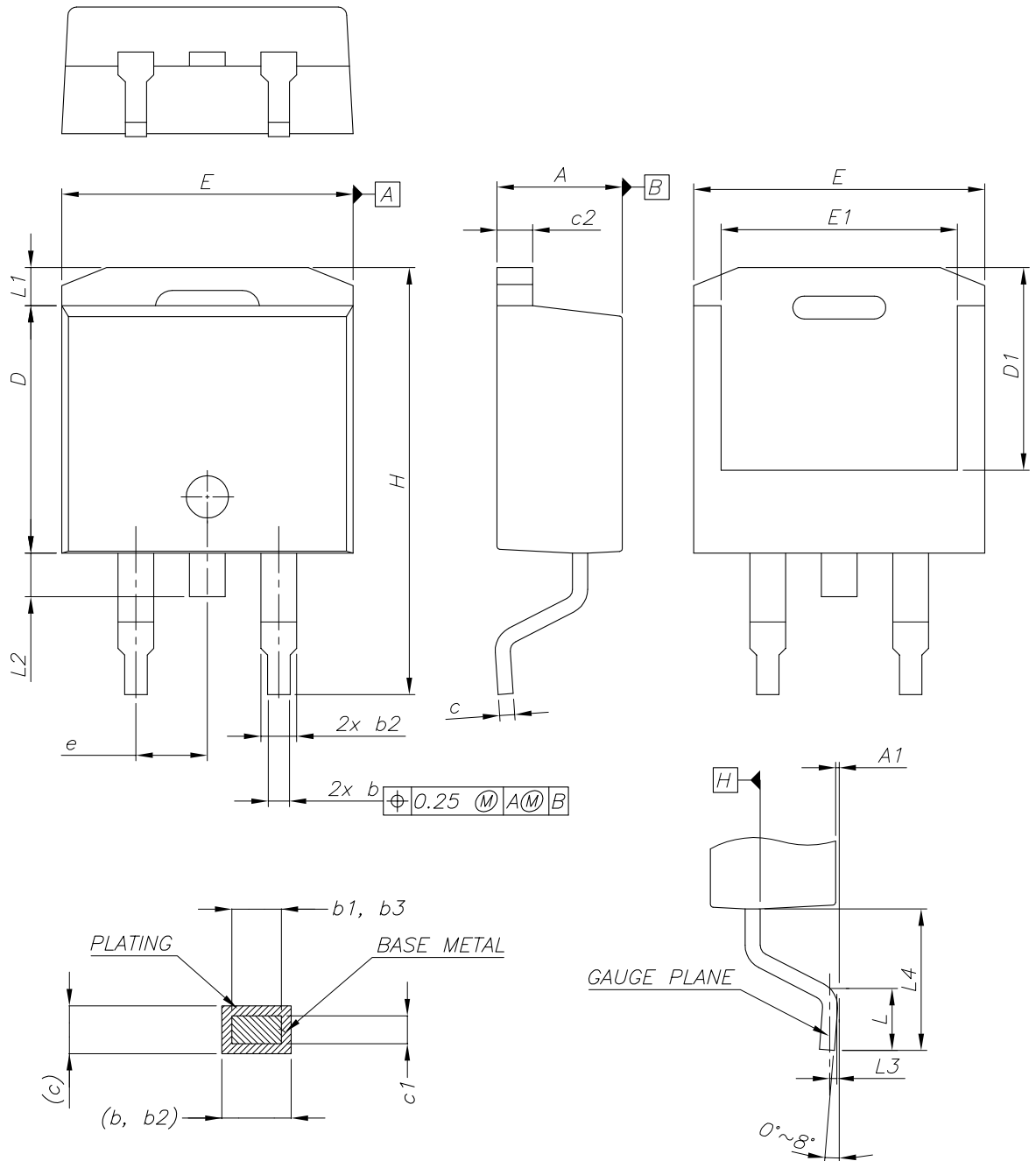
0079457\_24

**Table 9. D<sup>2</sup>PAK (TO-263) type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

### 4.3 D<sup>2</sup>PAK (TO-263) type B package information

Figure 21. D<sup>2</sup>PAK (TO-263) type B package outline

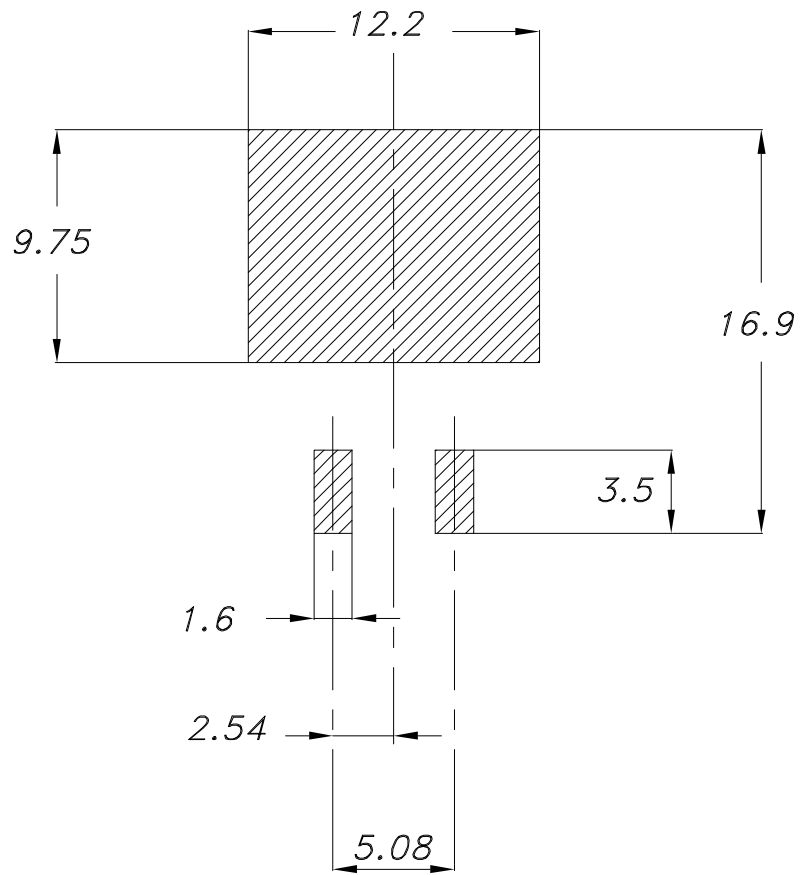


0079457\_24\_B

**Table 10. D<sup>2</sup>PAK (TO-263) type B mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.36		4.56
A1	0		0.25
b	0.70		0.90
b1	0.51		0.89
b2	1.17		1.37
b3	1.36		1.46
c	0.38		0.694
c1	0.38		0.534
c2	1.19		1.34
D	8.60		9.00
D1	6.90		7.50
E	10.15		10.55
E1	8.10		8.70
e	2.54 BSC		
H	15.00		15.60
L	1.90		2.50
L1			1.65
L2			1.78
L3		0.25	
L4	4.78		5.28

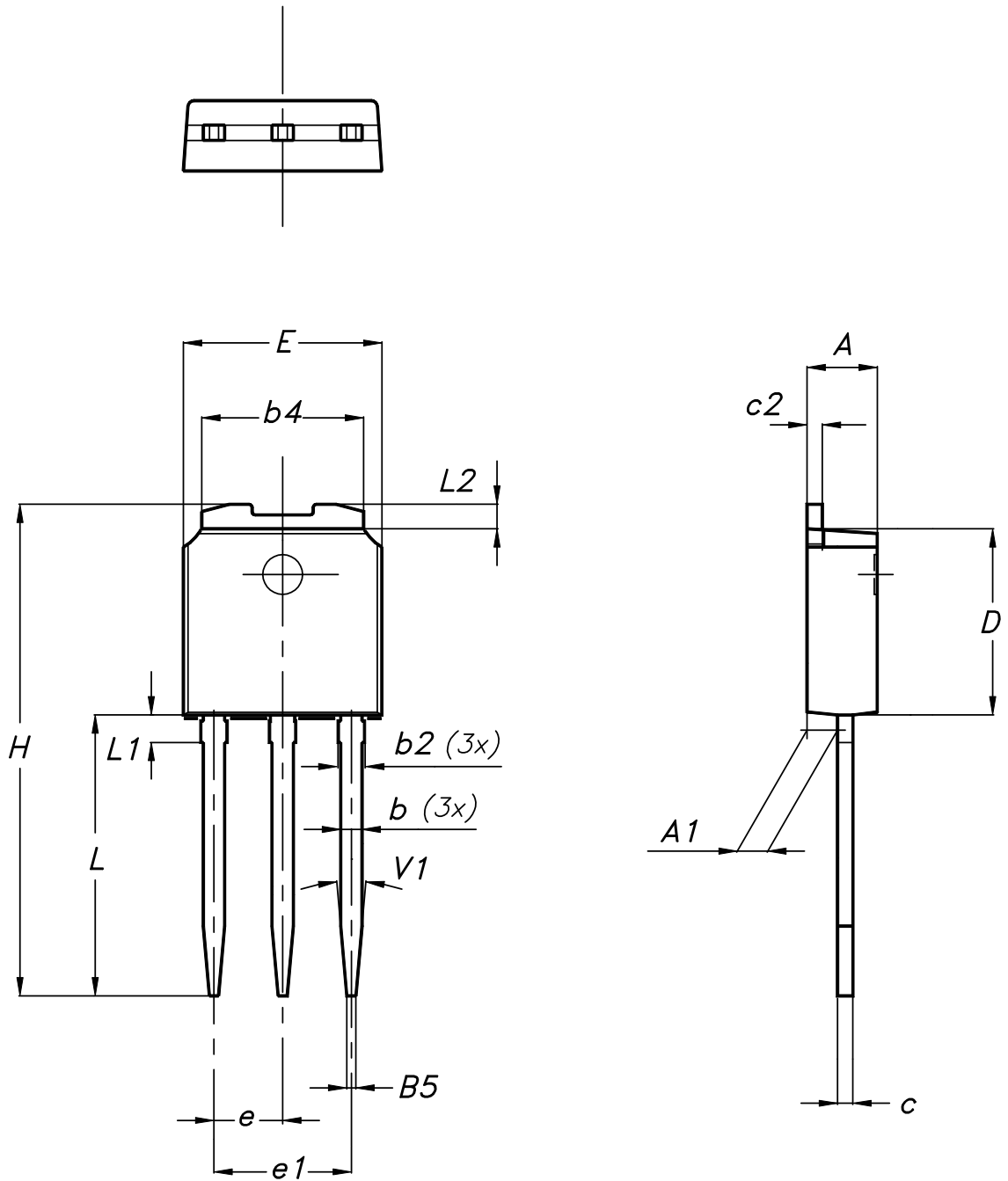
Figure 22. D<sup>2</sup>PAK (TO-263) recommended footprint (dimensions are in mm)



Footprint

#### 4.4 IPAk (TO-251) type A package information

Figure 23. IPAk (TO-251) type A package outline



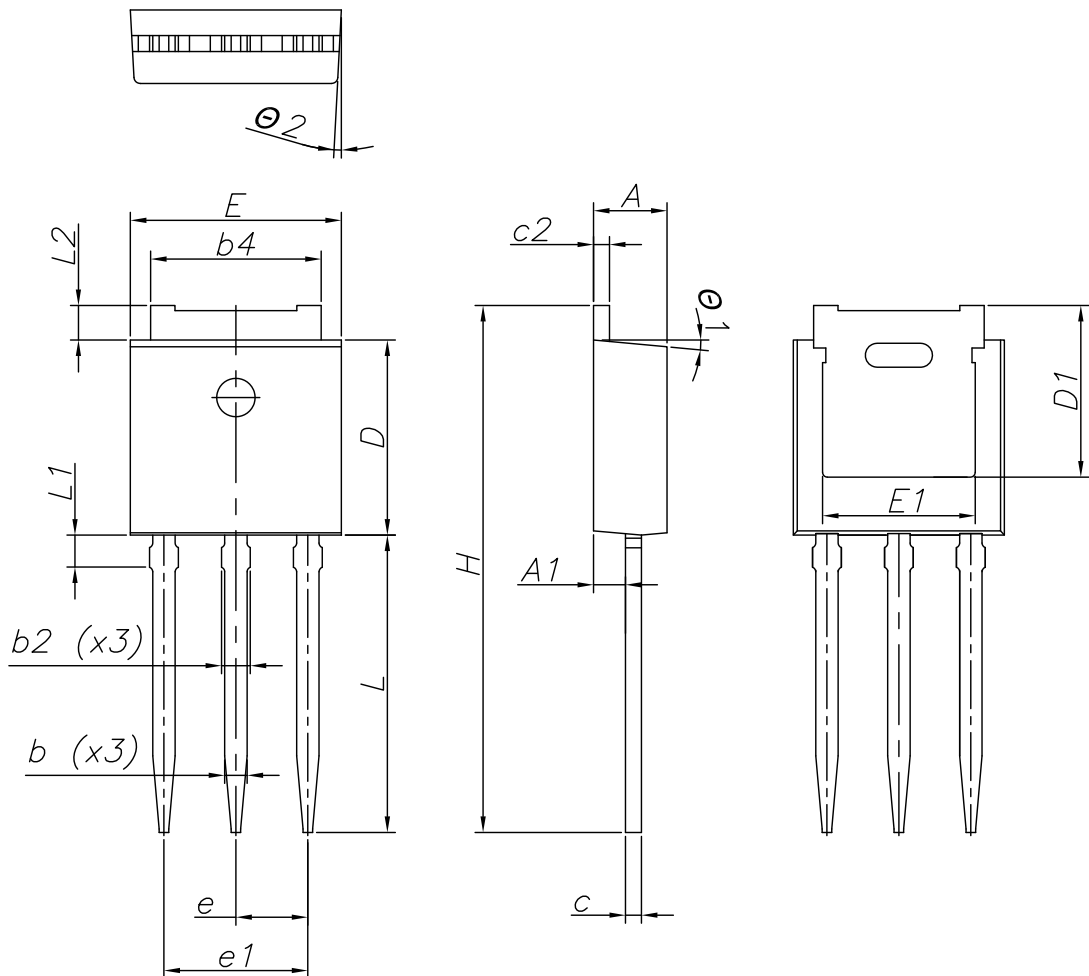
0068771\_IK\_typeA\_rev14

**Table 11. IPAK (TO-251) type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

#### 4.5 IPAK (TO-251) type C package information

Figure 24. IPAK (TO-251) type C package outline



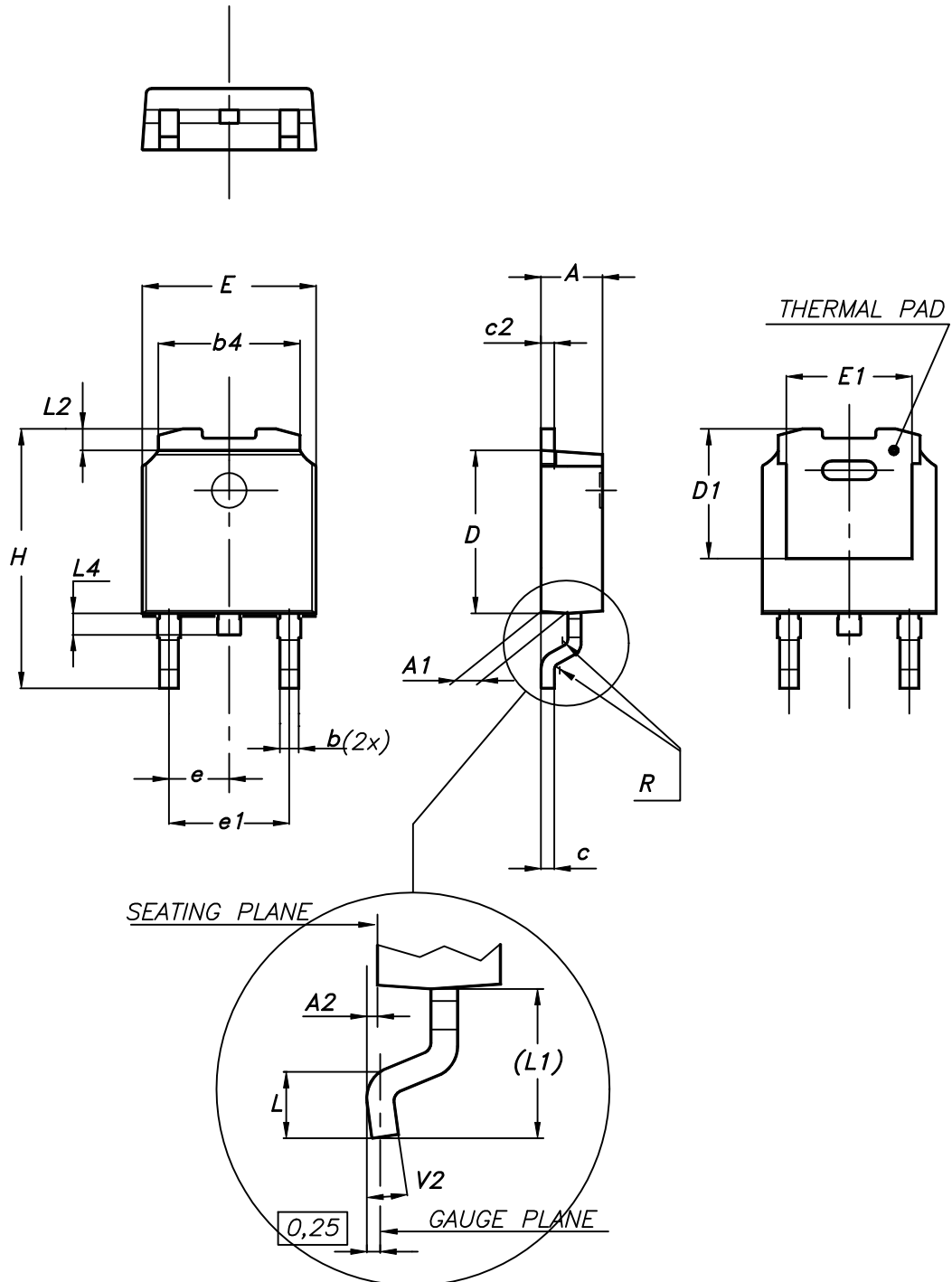
0068771\_IK\_typeC\_rev14

**Table 12. IPAK (TO-251) type C package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

4.6 DPAK (TO-252) type A2 package information

Figure 25. DPAK (TO-252) type A2 package outline



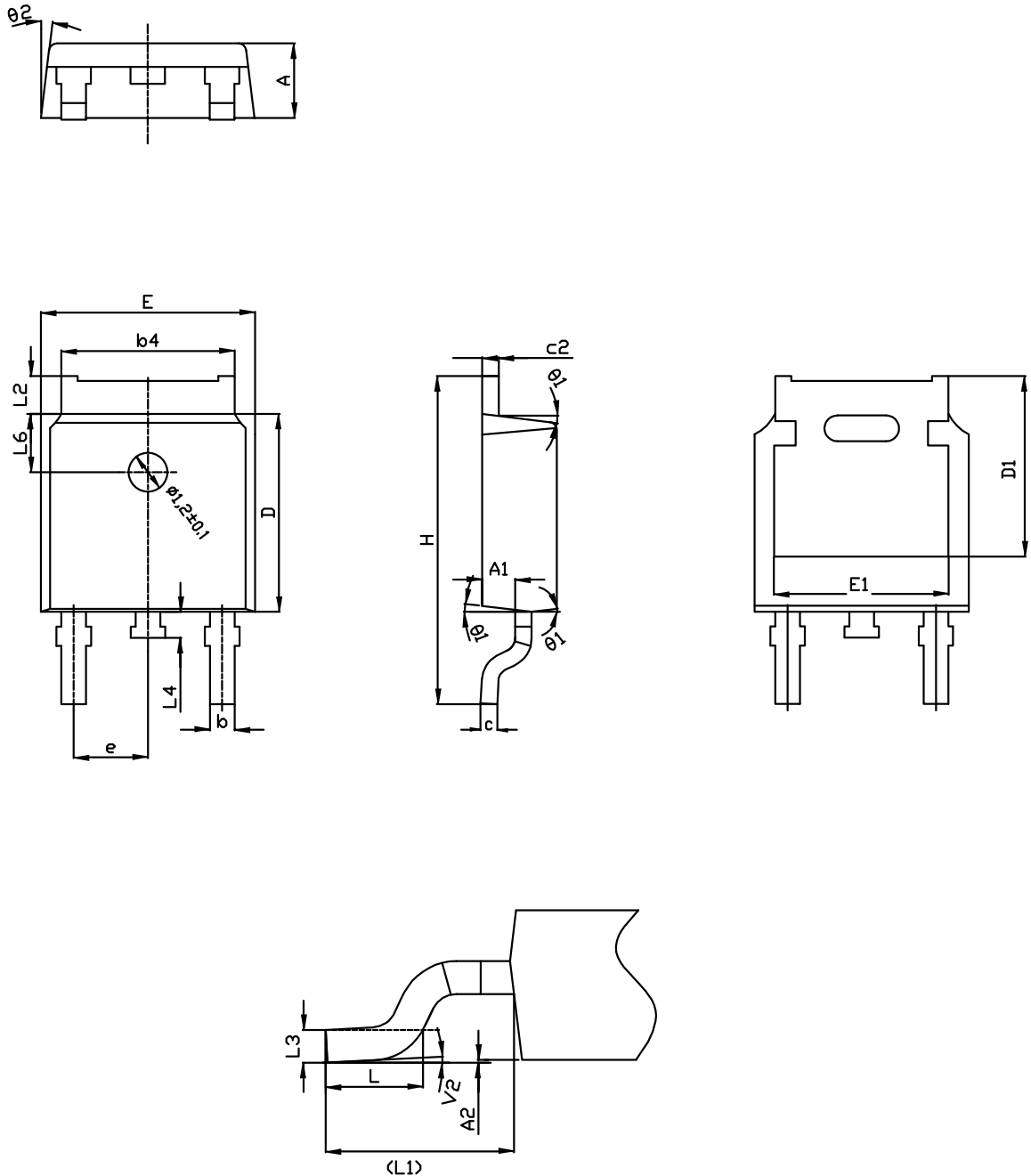
0068772\_type-A2\_rev24

**Table 13. DPAK (TO-252) type A2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

#### 4.7 DPAK (TO-252) type C2 package information

Figure 26. DPAK (TO-252) type C2 package outline



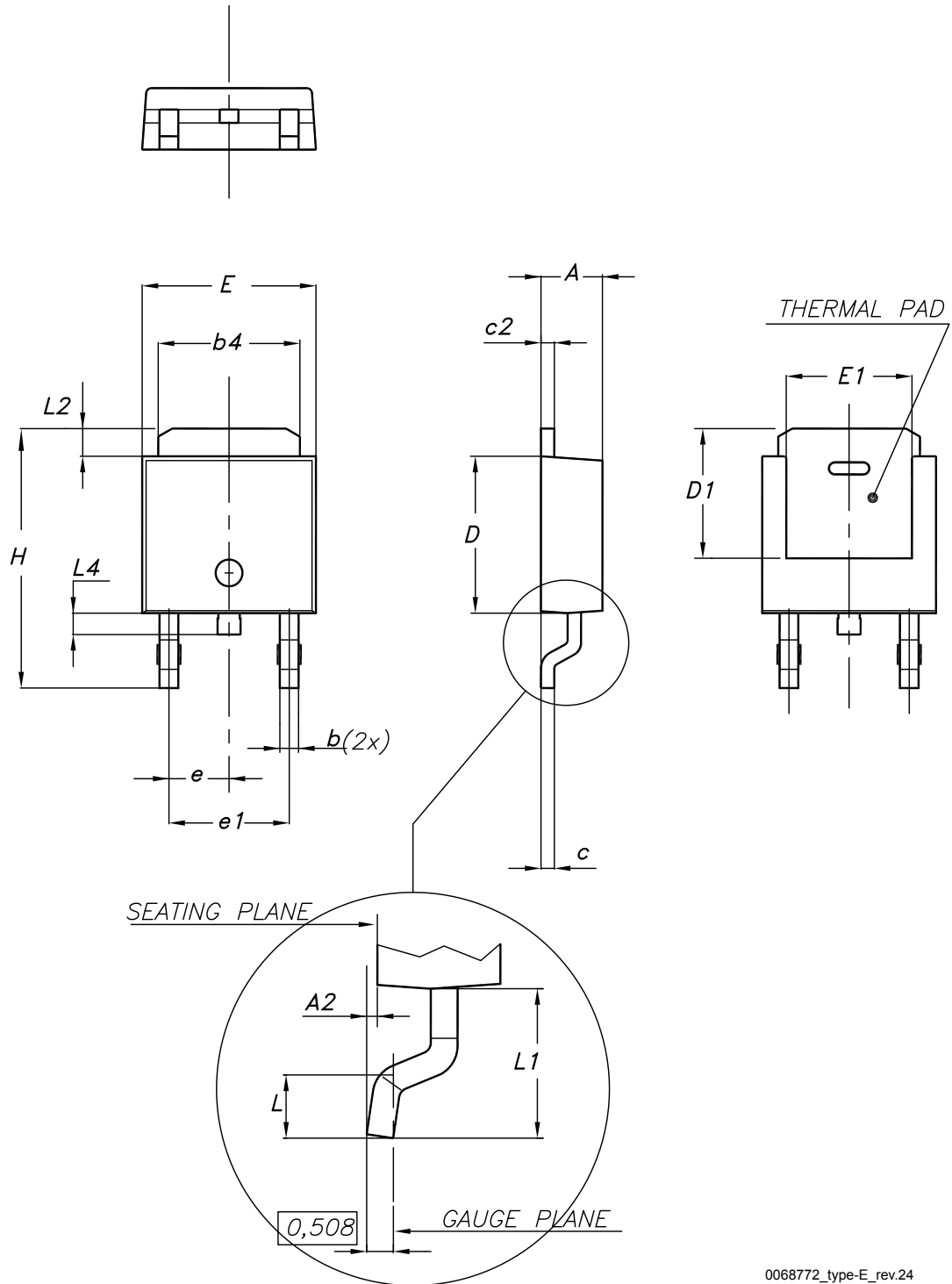
0068772\_C2\_24

**Table 14. DPAK (TO-252) type C2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.10		5.60
E	6.50	6.60	6.70
E1	5.20		5.50
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

### 4.8 DPAK (TO-252) type E package information

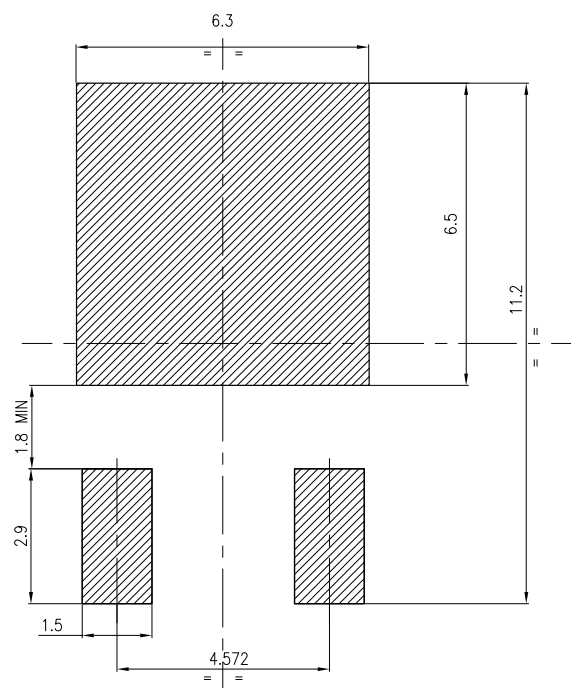
Figure 27. DPAK (TO-252) type E package outline



0068772\_type-E\_rev.24

**Table 15. DPAK (TO-252) type E mechanical data**

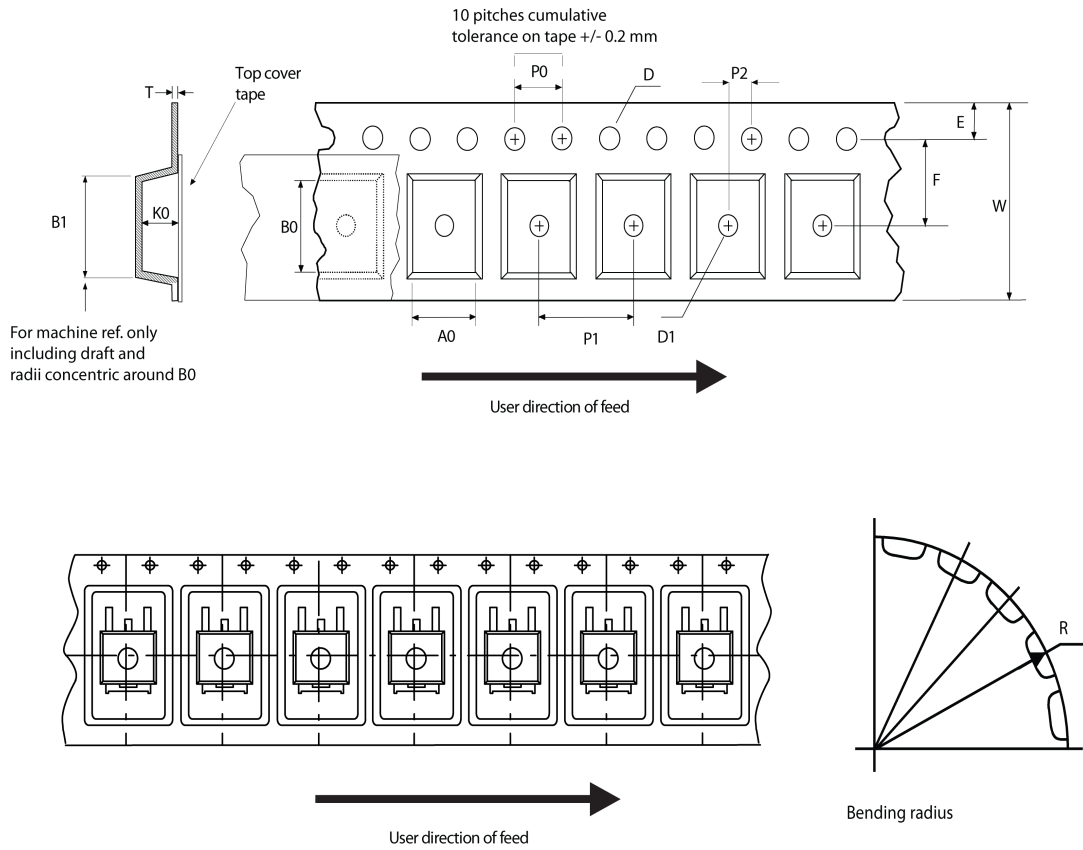
Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

**Figure 28. DPAK (TO-252) recommended footprint (dimensions are in mm)**


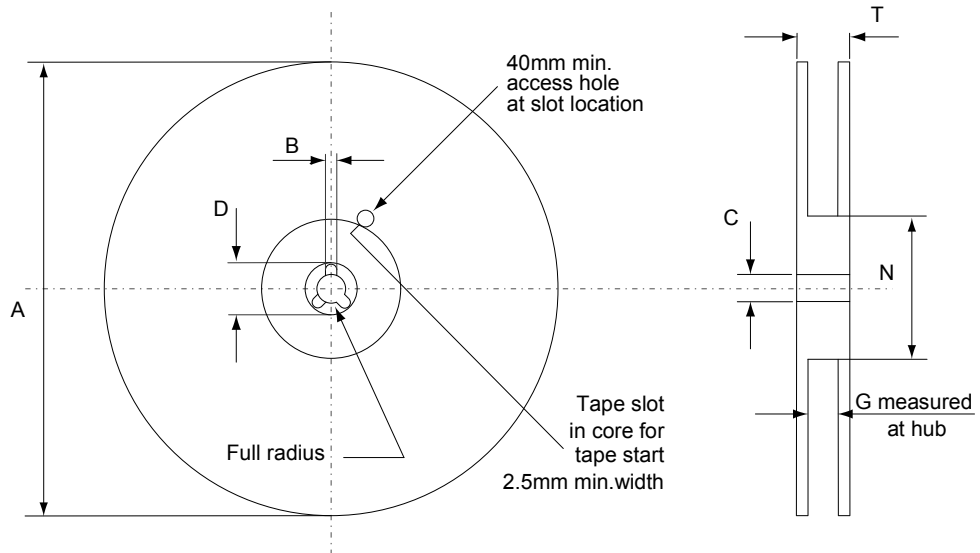
FP\_0068772\_24

## 4.9 D<sup>2</sup>PAK and DPAK packing information

Figure 29. Tape outline



AM08852v1

**Figure 30. Reel outline**


AM06038v1

**Table 16. D<sup>2</sup>PAK tape and reel mechanical data**

Tape			Reel			
Dim.	mm		Dim.	mm		
	Min.	Max.		Min.	Max.	
A0	10.5	10.7	A		330	
B0	15.7	15.9	B	1.5		
D	1.5	1.6	C	12.8	13.2	
D1	1.59	1.61	D	20.2		
E	1.65	1.85	G	24.4	26.4	
F	11.4	11.6	N	100		
K0	4.8	5.0	T		30.4	
P0	3.9	4.1	Base quantity Bulk quantity			
P1	11.9	12.1				1000
P2	1.9	2.1				1000
R	50					
T	0.25	0.35				
W	23.7	24.3				

**Table 17. DPAK tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

## 5 Ordering information

**Table 18. Order codes**

Order code	Marking	Package	Packing
STB4NK60Z-1	B4NK60Z	I <sup>2</sup> PAK	Tube
STB4NK60ZT4		D <sup>2</sup> PAK	Tape and reel
STD4NK60Z-1	D4NK60Z	IPAK	Tube
STD4NK60ZT4		DPAK	Tape and reel

## Revision history

**Table 19. Document revision history**

Date	Version	Changes
25-Oct-2006	4	Document reformatted no content change.
04-Mar-2008	5	Modified TO-220 and TO-220FP mechanical data.
16-Apr-2008	6	Minor text changes to improve readability.
11-Jul-2011	7	Updated package mechanical data <i>Section 4</i> and packaging mechanical data <i>Section 4</i> .
18-Jul-2013	8	<ul style="list-style-type: none"> <li>– Minor text changes</li> <li>– The part numbers STP4NK60Z and STP4NK60ZFP have been moved to a separate datasheet</li> <li>– Updated: <i>Section 4: Package mechanical data</i> and <i>Section 4: Package mechanical data</i></li> </ul>
05-Apr-2018	9	<p>Removed maturity status indication from cover page. The document status is production data.</p> <p>Updated part numbers.</p> <p>Updated <a href="#">Table 1. Absolute maximum ratings</a>, <a href="#">Table 4. On/off states</a>, <a href="#">Table 5. Dynamic</a>, <a href="#">Table 6. Source-drain diode</a> and <a href="#">Table 7. Gate-source Zener diode</a>.</p> <p>Updated <a href="#">Section 2.1 Electrical characteristics (curves)</a> and <a href="#">Section 4 Package information</a>.</p> <p>Minor text changes.</p>

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